

Product data sheet

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT186A (TO-220F) "full pack" plastic package. The "series D" triac balances the requirements of commutation performance and gate sensitivity. This "very sensitive gate" "series D" is intended for interfacing with low power drivers including microcontrollers.

## 2. Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with very sensitive gate
- High voltage capability
- Isolated mounting base package
- Planar technology for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very sensitive gate for easy logic level triggering

### 3. Applications

- General purpose motor controls
- Large and small appliances (White Goods)
- Loads such as contactors, circuit breakers, valves, dispensers and door locks
- Lower-power highly inductive, resistive and safety loads

### 4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage		-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 20 ms; <u>Fig. 4; Fig. 5</u>	-	-	14	A
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 110 \text{ °C}$ ; Fig. 1; Fig. 2; Fig. 3	-	-	2	A
Static charact	eristics					
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.25	-	5	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.25	-	5	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.25	-	5	mA

# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2
2	T2	main terminal 2		sym051
3	G	gate		
mb	n.c.	mounting base; isolated		
			TO-220F (SOT186A)	

# 6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
BTA202X-800D	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

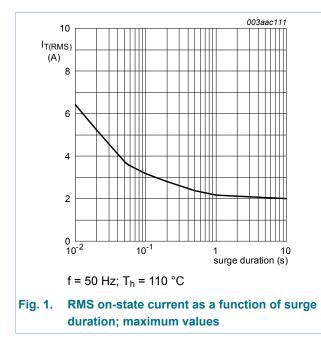
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### 7. Limiting values

#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 110 \text{ °C}$ ; Fig. 1; Fig. 2; Fig. 3	-	2	A
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; \text{Fig. 4}; \text{Fig. 5}$	-	14	A
		full sine wave; $T_{j(init)} = 25 \text{ °C};$ t <sub>p</sub> = 16.7 ms	-	15.4	A
l <sup>2</sup> t	I2t for fusing	t <sub>p</sub> = 10 ms; SIN	-	0.98	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T$ = 1.5 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/µs	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	А
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C



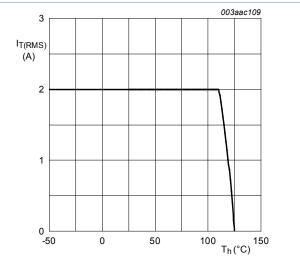
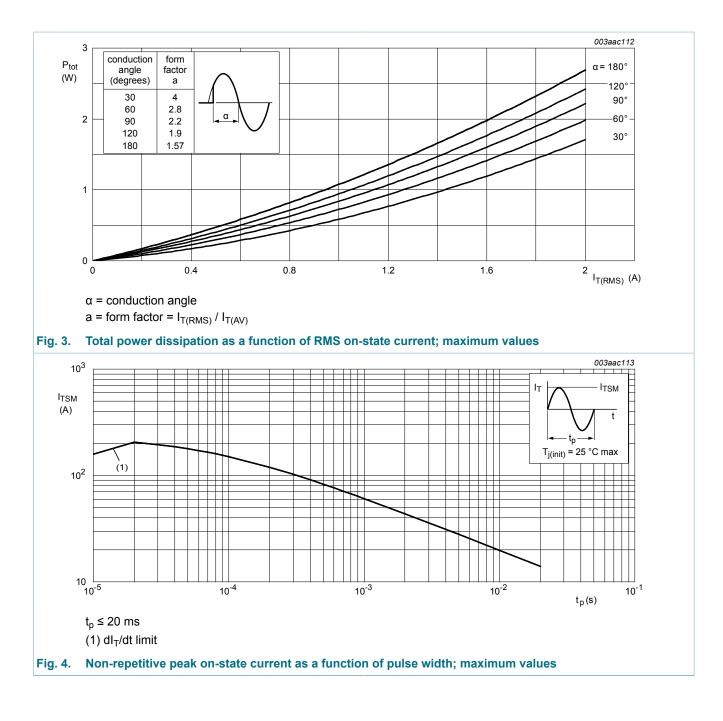


Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values

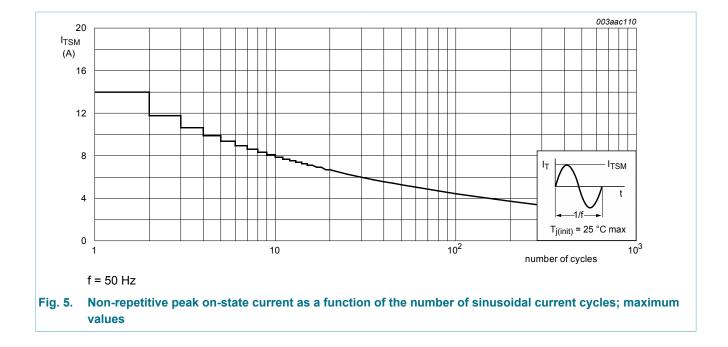
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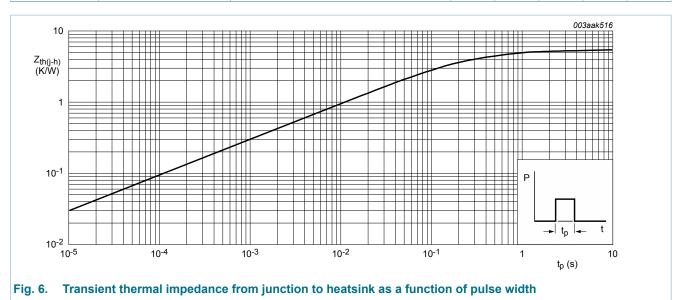
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## 8. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to heatsink	full cycle; with heatsink compound; Fig. 6	-	-	5.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	55	-	K/W



### 9. Isolation characteristics

Table 6. Isolation characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; T <sub>h</sub> = 25 °C		-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz		-	10	-	pF

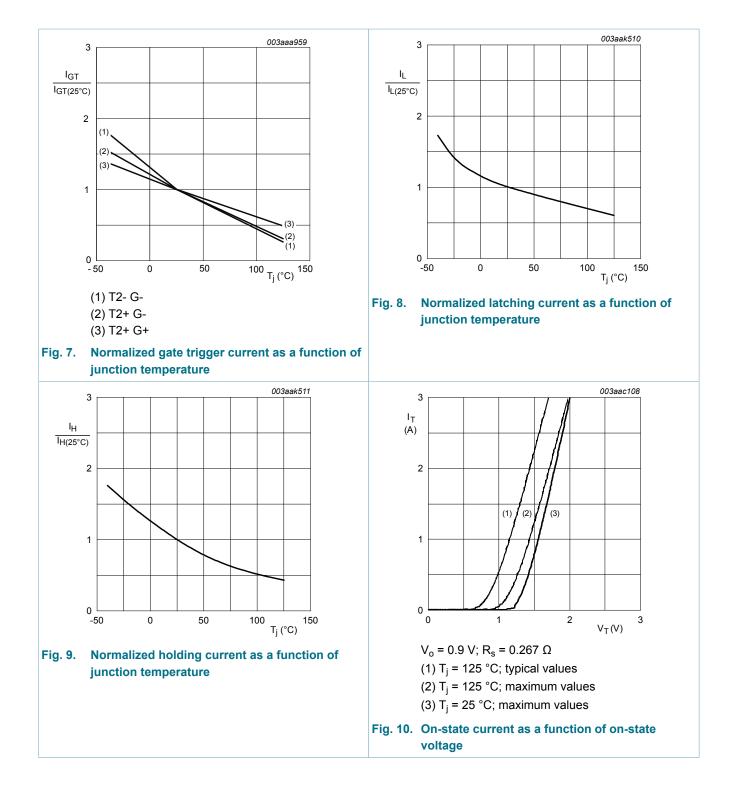
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## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		· · ·			
I <sub>GT</sub> g	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.25	-	5	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2+ G-};$ T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.25	-	5	mA
		$V_D$ = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.25	-	5	mA
ΙL	latching current	V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	5	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	5	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	5	mA
VT	on-state voltage	I <sub>T</sub> = 3 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.63	2	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; Fig. 11	-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; Fig. 11	0.2	0.3	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic cł	naracteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; T <sub>j</sub> = 125 °C; R <sub>GT1</sub> = 220 Ω; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform	-	350	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$\label{eq:VD} \begin{split} V_D &= 400 \text{ V};  \text{T}_{j} = 125 ^\circ\text{C};  \text{I}_{\text{T}(\text{RMS})} = 2 \text{ A}; \\ dV_{\text{com}}/dt &= 20  \text{V}/\mu\text{s};  \text{(snubberless} \\ \text{condition}); \text{ gate open circuit} \end{split}$	1	-	-	A/m
		$V_D$ = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 2 A; dV <sub>com</sub> /dt = 10 V/µs; gate open circuit	1.2	-	-	A/m

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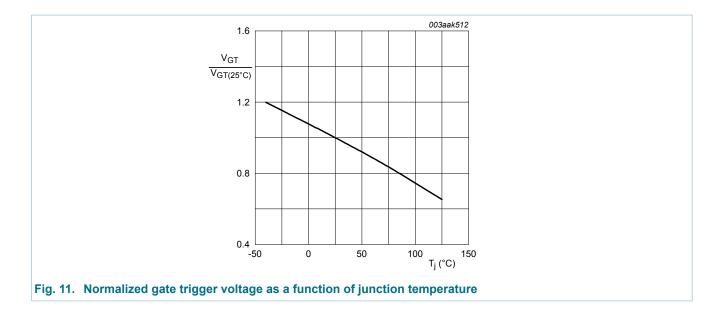


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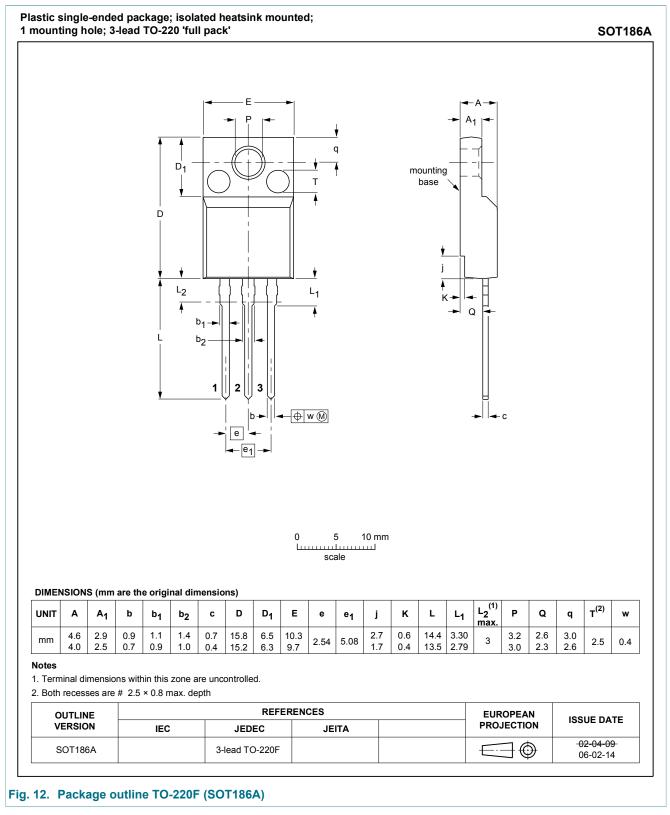
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### **11. Package outline**



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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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